

# YJ Planar Schottky Barrier Diode Die Specification

40V 0.04A,9mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB009L040AG-155A

## Main Products Characteristics

- Average forward current:  $I_F(AV) = 0.04A$
- Maximum operating junction temperature:  $T_j = 125\text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um

## Maximum Ratings

## Static Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

$I_F = 0.04A$

Pulse Test:  $t_p = 800\text{ }\mu\text{s}$ , 2%

## Device Schematics and Outline Drawing

Die Thickness \*

Die Size \*\*

Top Metal Pad

Active Area

Top Metal

Back Metal

Steet width

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

does not guarantee device performance after assembly.